

MCCF1709 MCCF1709C

MONOLITHIC OPERATIONAL AMPLIFIER FLIP-CHIP

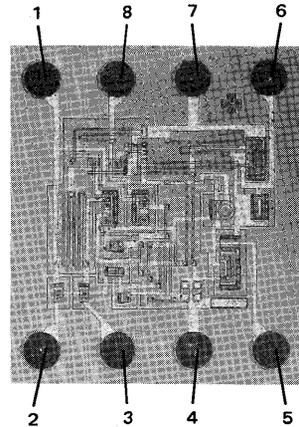
... designed for use as a summing amplifier, integrator, or amplifier with operating characteristics as a function of the external feedback components.

The MCCF1709 and MCCF1709C employ phosphorsilicate passivation that protects the entire die surface area, including metalization interconnects. The bumps are 95-5 solder on a chrome-copper-gold base. The interconnecting metalization is evaporated aluminum.

- High-Performance Open Loop Gain Characteristics
 $A_{VOL} = 45,000$ typical
- Low Temperature Drift $- \pm 3.0 \mu V / ^\circ C$
- Large Output Voltage Swing $- \pm 14 V$ typical @ $\pm 15 V$ Supply
- Low Output Impedance $- z_o = 150$ ohms typical

FLIP-CHIP OPERATIONAL AMPLIFIER

MONOLITHIC SILICON INTEGRATED CIRCUIT



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MAXIMUM RATINGS ($T_A = +25^\circ C$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC} V_{EE}	+18 -18	Vdc
Differential Input Signal	V_{ID}	± 5.0	Volts
Common Mode Input Swing	V_{IC}	$\pm V_S$	Volts
Load Current	I_L	10	mA
Output Short Circuit Duration	t_S	5.0	s
Operating Temperature Range	MCCF1709 MCCF1709C T_A	-55 to +125 0 to +75	$^\circ C$
Junction Temperature Range	T_J	-55 to +150	$^\circ C$

FIGURE 1 - CIRCUIT SCHEMATIC

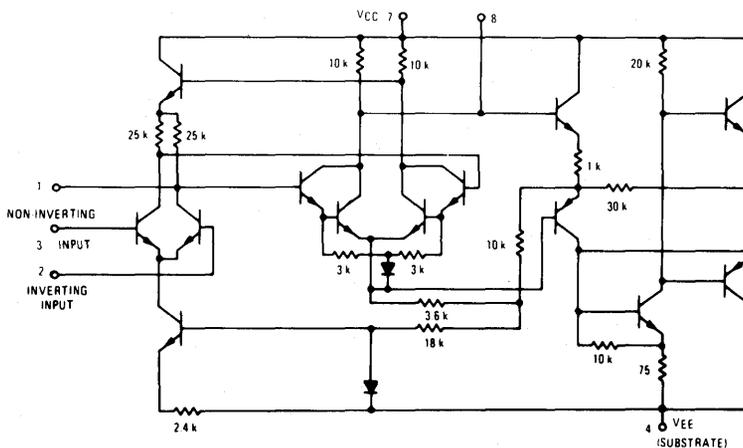
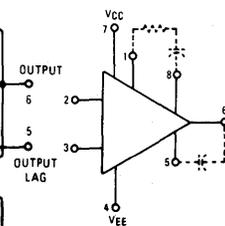


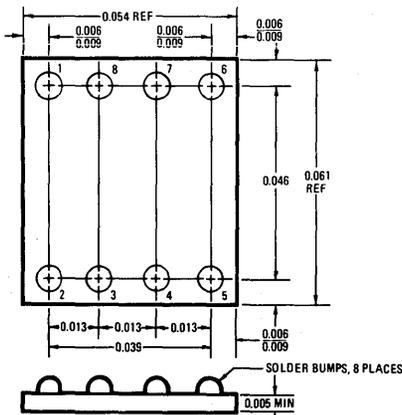
FIGURE 2 - EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS ($V_{CC} = +15$ Vdc, $V_{EE} = -15$ Vdc, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	MCCF1709			MCCF1709C			Unit
		Min	Typ	Max	Min	Typ	Max	
Open Loop Voltage Gain ($V_O = \pm 10\text{V}$)	A_{VOL}	25,000	45,000	70,000	15,000	45,000	—	—
Output Impedance ($f = 20$ Hz)	z_O	—	150	—	—	150	—	Ω
Input Impedance ($f = 20$ Hz)	z_{in}	—	400	—	—	250	—	$k\Omega$
Output Voltage Swing ($R_L = 10$ k Ω) ($R_L = 2.0$ k Ω)	V_O	± 12 ± 10	± 14 ± 13	— —	± 12 ± 10	± 14 ± 13	— —	V_{peak}
Input Common-Mode Voltage Swing	V_{IC}	—	± 10	—	—	± 10	—	V_{peak}
Common-Mode Rejection Ratio ($f = 20$ Hz)	CMRR	—	90	—	—	90	—	dB
Input Bias Current	I_{IB}	—	0.2	0.5	—	0.3	1.5	μA
Input Offset Current	$ I_{IO} $	—	0.05	0.2	—	0.1	0.5	μA
Input Offset Voltage	$ V_{IO} $	—	1.0	5.0	—	2.0	7.5	mV
Step Response								
Gain = 100, 5.0% overshoot	t_{THL}	—	0.8	—	—	0.8	—	μs
	t_d	—	0.38	—	—	0.38	—	μs
	dV_O/dt	—	12	—	—	12	—	$\text{V}/\mu\text{s}$
Gain = 10, 10% overshoot	t_{THL}	—	0.6	—	—	0.6	—	μs
	t_d	—	0.34	—	—	0.34	—	μs
	dV_O/dt	—	1.7	—	—	1.7	—	$\text{V}/\mu\text{s}$
Gain = 1, 5.0% overshoot	t_{THL}	—	2.2	—	—	2.2	—	μs
	t_d	—	1.3	—	—	1.3	—	μs
	dV_O/dt	—	0.25	—	—	0.25	—	$\text{V}/\mu\text{s}$
Power Supply Current	I_{DCC}	—	2.7	5.5	—	2.7	6.7	mA_{dc}
	I_{DEE}	—	2.7	5.5	—	2.7	6.7	mA_{dc}
DC Quiescent Power Dissipation (Power Supply = ± 15 V, $V_O = 0$)	P_D	—	80	165	—	80	200	mW
Positive Supply Sensitivity (V_{EE} constant)	S^+	—	25	150	—	25	200	$\mu\text{V}/\text{V}$
Negative Supply Sensitivity (V_{CC} constant)	S^-	—	25	150	—	25	200	$\mu\text{V}/\text{V}$

See current MC1709/1709C data sheet for additional information.



Bump Dia. at Base: 0.006 ± 0.001 in. Bump Height: 0.0040 ± 0.0005 in.
Each bump centerline to be located within 0.001 in. of its true position with respect to any other bump centerline.

PACKAGING AND HANDLING

The popular 1709 type operational amplifier is now available in three chip forms: 1) conventional chips, 2) beam-lead chips and 3) flip-chips, as well as in a variety of plastic and hermetic packages. The flip-chip consists of a silicon chip with solder bumps on the geometry surface to provide easy mechanical mounting and electrical connection. These devices are protected by a thin layer of phosphorsilicate passivation which covers the interconnect metalization and active areas of the die.

Care must be exercised when removing the dice from the shipping carrier to avoid scratching the solder bumps. A vacuum pickup is useful for the handling of dice. Tweezers are not recommended for this purpose.

The non-spill type shipping carrier consists of a compartmentalized tray and fitted cover. Die are placed in the carrier with geometry side up.